Dual N-channel 40 V, 29 m $\Omega$  logic level MOSFET

# **Pinning information**

Table 2. **Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	8 7 6 5	D1 D1 D2 D2
2	G1	gate1	\\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\	
3	S2	source2		
4	G2	gate2		
5	D2	drain2		
6	D2	drain2	ÜÜÜ	mbk725
7	D1	drain1	1 2 3 4 LFPAK56D (SOT1205)	
8	D1	drain1	2	

# **Ordering information**

Table 3. **Ordering information** 

Type number	Package				
	Name	Description	Version		
BUK9K25-40E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205		

#### **Marking** 7.

Table 4. **Marking codes** 

Type number	Marking code
BUK9K25-40E	92540E

#### **Limiting values** 8.

Table 5. **Limiting values** 

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	40	V
$V_{DGR}$	drain-gate voltage	$R_{GS}$ = 20 k $\Omega$		-	40	V
$V_{GS}$	gate-source voltage	T <sub>j</sub> ≤ 175 °C; Pulsed	[1][2]	-15	15	V
		T <sub>j</sub> ≤ 175 °C; DC		-10	10	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 5 V; <u>Fig. 1</u>		-	18.2	Α
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 5 V; <u>Fig. 1</u>		-	16.6	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; Fig. 4		-	94	Α
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Symbol	Parameter	Conditions		Min	Max	Unit
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	32	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	in diode FET1 and FET2					
Is	source current	T <sub>mb</sub> = 25 °C		-	18.2	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	94	Α
Avalanche	Ruggedness FET1 and FET2	'				,
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 18.2 A; $V_{sup} \le 40 \text{ V}$ ; $V_{GS}$ = 10 V; $V_{j(init)}$ = 25 °C; Fig. 3	[3][4]	-	15	mJ

- [1] Accumulated Pulse duration up to 50 hours delivers zero defect ppm.
- [2] Significantly longer life times are achieved by lowering T<sub>i</sub> and or V<sub>GS</sub>.
- [3] Refer to application note AN10273 for further information
- [4] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

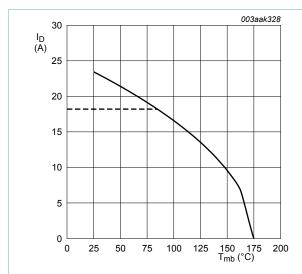


Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 5V$$

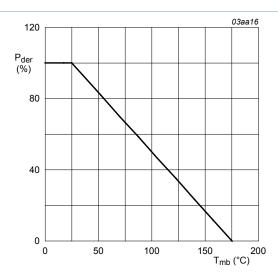


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

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# Dual N-channel 40 V, 29 m $\Omega$ logic level MOSFET

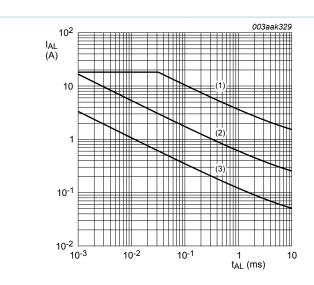


Fig. 3. Avalanche rating; avalanche current as a function of avalanche time

(1) Single-pulse;  $T_j = 25 \,^{\circ}C$ .

(2) Single-pulse;  $T_j = 150 \,^{\circ}C$ .

(3) Repetitive.

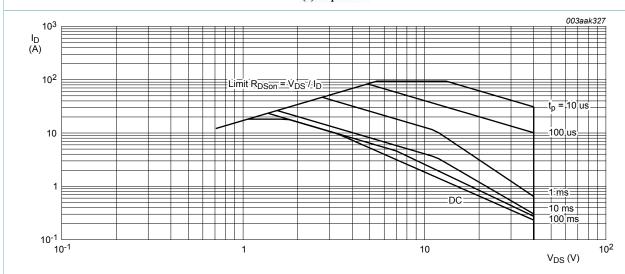


Fig. 4. Safe operating area; continuous and peak drain current as a function of drain-source voltage

 $T_{mb} = 25 \,^{\circ}C; I_{DM}$  is single pulse

# 9. Thermal characteristics

Table 6. Thermal characteristics

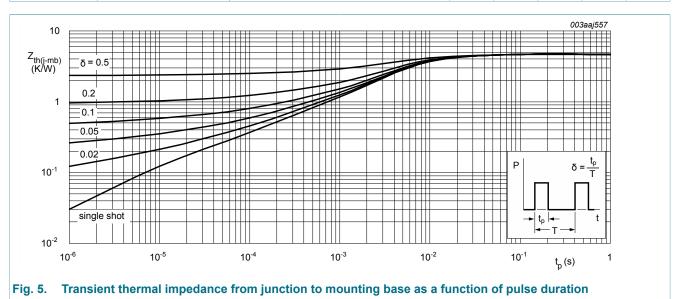
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	-	4.68	K/W

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## Dual N-channel 40 V, 29 m $\Omega$ logic level MOSFET

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W



# 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics FET1 and FET2		,			_
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	36	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	40	-	-	V
()	gate-source threshold voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C; Fig. 9; Fig. 10	1.4	1.7	2.1	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; Fig. 9; Fig. 10	0.5	-	-	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; Fig. 9; Fig. 10	-	-	2.45	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
		V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.02	1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	24	29	mΩ
	resistance	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 175 °C; Fig. 11; Fig. 12	-	48.2	58	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$	-	19	24	mΩ
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic cl	haracteristics FET1 and FE	T2				
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 5 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 5 V;	-	6.3	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	1.4	-	nC
$Q_{GD}$	gate-drain charge		-	2.4	-	nC
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz; T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	-	528	701	pF
C <sub>oss</sub>	output capacitance		-	95	114	pF
C <sub>rss</sub>	reverse transfer capacitance		-	56	76	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 32 \text{ V}; R_L = 6.4 \Omega; V_{GS} = 5 \text{ V};$	-	6.2	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C; I_D = 5 A$	-	9.2	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	10.8	-	ns
t <sub>f</sub>	fall time		-	8.9	-	ns
Source-dra	in diode FET1 and FET2					
V <sub>SD</sub>	source-drain voltage	$I_S = 5 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; Fig. 16$	-	0.83	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 5 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$ $V_{DS} = 20 \text{ V}; T_j = 25 \text{ °C}$	-	15.9	-	ns
Q <sub>r</sub>	recovered charge		-	7.6	-	nC

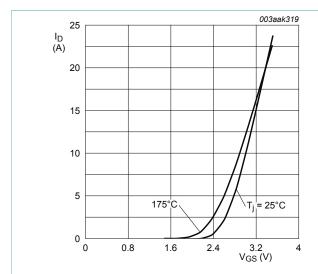


Fig. 6. Transfer characteristics; drain current as a function of gate-source voltage; typical values

 $V_{DS} = 10V$ 

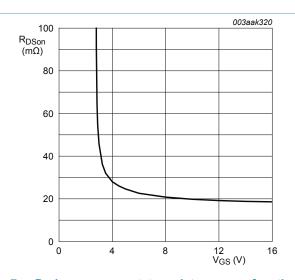


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25^{\circ}C; I_D = 5A$ 

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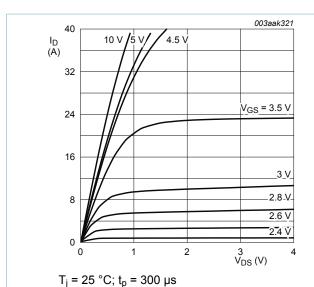


Fig. 8. Output characteristics; drain current as a function of drain-source voltage; typical values

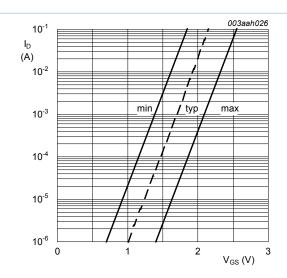


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25$$
°C;  $V_{DS} = 5V$ 

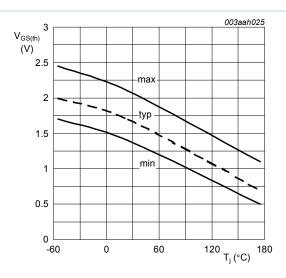
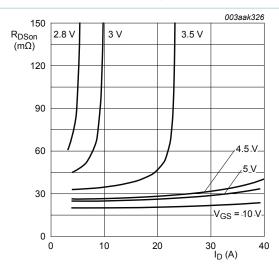


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$$



 $T_i$  = 25 °C;  $t_p$  = 300  $\mu$ s

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

# Dual N-channel 40 V, 29 m $\Omega$ logic level MOSFET

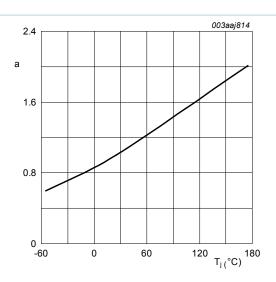


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon}(25^{\circ}C)}$$

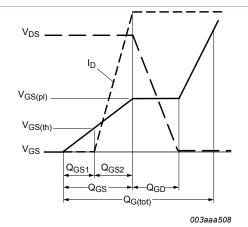


Fig. 14. Gate charge waveform definitions

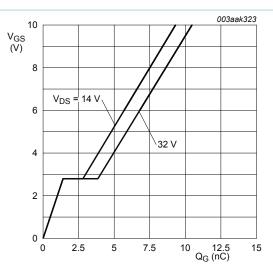


Fig. 13. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25$$
°C;  $I_D = 5A$ 

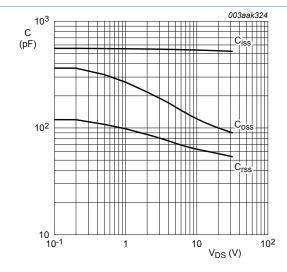


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0}V; f = \mathbf{1}MHz$$

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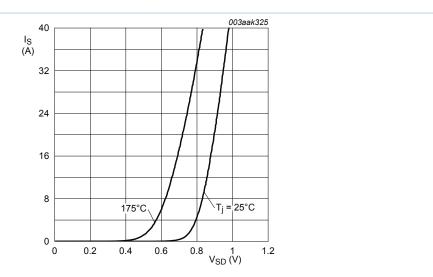
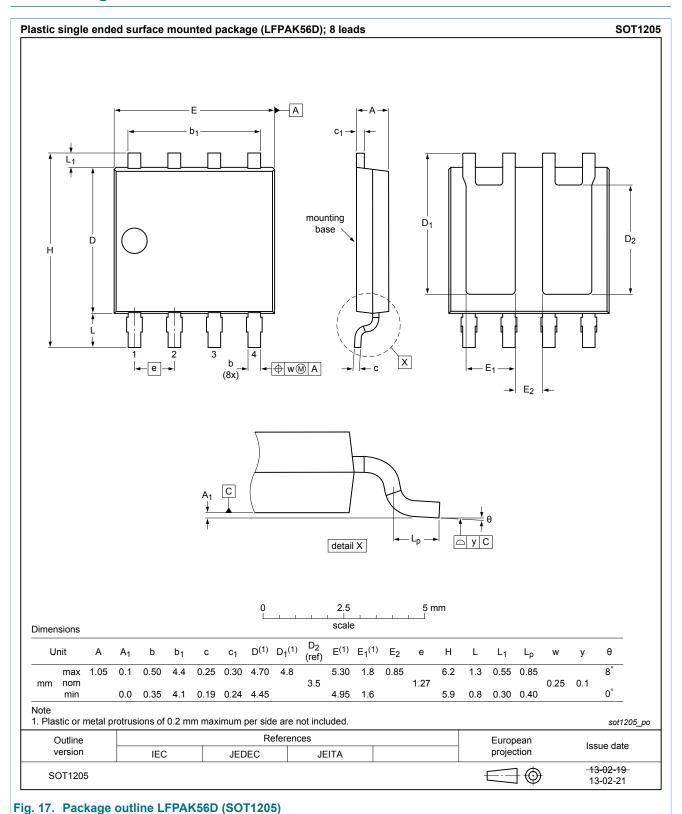


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

Dual N-channel 40 V, 29 m $\Omega$  logic level MOSFET

# 11. Package outline



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### Dual N-channel 40 V, 29 mΩ logic level MOSFET

# 12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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